	Туре	L#	Hits	Search Text	DBs	Time Stamp	en	De	Er ro rs
1	IS&R	L1	2	("20030089899") .PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	2005/03/16 15:12			
2	IS&R	L2	2	("20040145053") .PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/16 15:13			
3	IS&R	L 3	2	("6670693").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/16 15:13			
4	BRS	L4	46	nano\$ with wide with (bandgap or band near gap) with semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/16 15:16			
5	BRS	L5	38	or band near gap) with semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/16 15:18			

	Туре	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	De fi	Er ro rs
6	BRS	L6	31	gap) with semiconductor and (heat\$5 or thermal) and	I. I D() •	2005/03/16 15:20			

	Type	L#	Hits	Search Text	DBs	Time Stamp	Co mm en ts	De fi	Er ro rs
1	IS&R	L1	2	ŀ	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/16 15:12			
2	IS&R	L2	2	("20040145053") .PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/16 15:13			
3	IS&R	L3	2	("6670693").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/16 15:13			
4	BRS	L4	46	nano\$ with wide with (bandgap or band near gap) with semiconductor	TICDAT. EDO.	2005/03/16 15:16			
5	BRS	L5		nano\$ with wide with (bandgap or band near gap) with semiconductor and (heat\$5 or thermal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/16 17:38			

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	Type	L#	Hits	Search Text	DBs	Time Stamp	Co mm en ts	De fi	Er ro rs
6	BRS	L6	31	gap) with semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/16 15:20			

	Type	L#	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro rs
7	BRS	L7			US-PGPUB; USPAT; USOCR	2005/03/16 17:37		

	Туре	L#	Hits	Search Text	DBs	Time Stamp	Co mm en ts	De	Er ro rs
8	BRS	L9	2	gap) with	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/16 17:39			
9	BRS	L8	28	or band near gap) with	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/16 17:44	,		
10	BRS	L10	146	with semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/16 17:46			

	Туре	L#	Hits		DBs	Time Stamp	Co mm en ts	De fi	Er
11	BRS	L11	7	wide with (bandgap or band near gap) with semiconductor with (heat\$5 or thermal or irradiat\$5 with (laser or beam)) with (source or drain or gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/16 18:02			
12	IS&R	L12	2	("6271576").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/16 18:00			
13	BRS	L13	0		DERWENT;	2005/03/16 18:03			

	Туре	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	De	Er ro rs
14	BRS	L14	7	band near gap) with	DERWENT;	2005/03/16 18:03			
15	BRS ,	L15		2003- 224203.NRAN.	DERWENT	2005/03/16 18:07			